FKS8016

N-Ch 80V Fast Switching MOSFETs

★ Super Low Gate Charge
★ 100% EAS Guaranteed
★ Green Device Available
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

Green

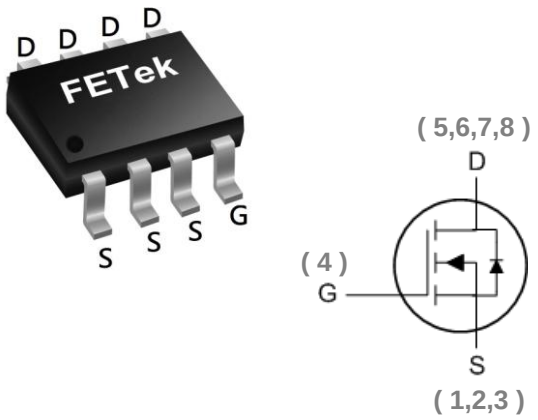
BVDSS	RDSON	ID
80V	12mΩ	11A

Description

The FKS8016 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The FKS8016 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

SOP8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	80	V
V_{GS}	Gate-Source Voltage	±20	V
I_D@T_A=25°C	Continuous Drain Current[1]	11	A
I_D@T_A=70°C	Continuous Drain Current[1]	9	A
I_{DM}	Pulsed Drain Current[2]	80	A
EAS	Single Pulse Avalanche Energy[3]	80	mJ
P_D@T_A=25°C	Total Power Dissipation[4]	2.8	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient [1](t≦10S)	---	45	°C/W
	Thermal Resistance Junction-ambient [1](Steady State)	---	85	°C/W

Electrical Characteristics (T_J=25 ℃, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=250uA	80	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V , I_D=8A	---	9.6	12	mΩ
		V_{GS}=4.5V, I_D=6A	---	12	14.5	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D =250uA	1.2	---	2.5	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}=64V , V_{GS}=0V , T_J=25℃	---	---	1	uA
		V_{DS}=64V , V_{GS}=0V , T_J=55℃	---	---	5	
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA
gfs	Forward Transconductance	V_{DS}=5V , I_D=10A	---	32	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f=1MHz	---	0.7	---	Ω
Q_g	Total Gate Charge (10V)	V_{DS}=64V , V_{GS}=10V , I_D=4A	---	60.9	---	nC
Q_{gs}	Gate-Source Charge		---	8.1	---	
Q_{gd}	Gate-Drain Charge		---	17.9	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=40V , V_{GS}=10V , R_G=3.3Ω, I_D=4A	---	12.2	---	ns
T_r	Rise Time		---	24.5	---	
$T_{d(off)}$	Turn-Off Delay Time		---	50.5	---	
T_f	Fall Time		---	17.6	---	
C_{iss}	Input Capacitance	V_{DS}=50V , V_{GS}=0V , f=1MHz	---	3120	---	pF
C_{oss}	Output Capacitance		---	140	---	
C_{rss}	Reverse Transfer Capacitance		---	110	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current[1,5]	V_G=V_D=0V , Force Current	---	---	62	A
V_{SD}	Diode Forward Voltage[2]	V_{GS}=0V , I_S=1A , T_J=25℃	---	---	1.2	V
t_{rr}	Reverse Recovery Time	I_F=4A , dI/dt=100A/μs , T_J=25℃	---	18.6	---	nS
Q_{rr}	Reverse Recovery Charge		---	65	---	nC

Note :
1.The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper.
2.The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3.The EAS data shows Max. rating . The test condition is V_{DD}=50V,V_{GS}=10V,L=0.1mH,I_{AS}=40A
4.The power dissipation is limited by 150℃ junction temperature
5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

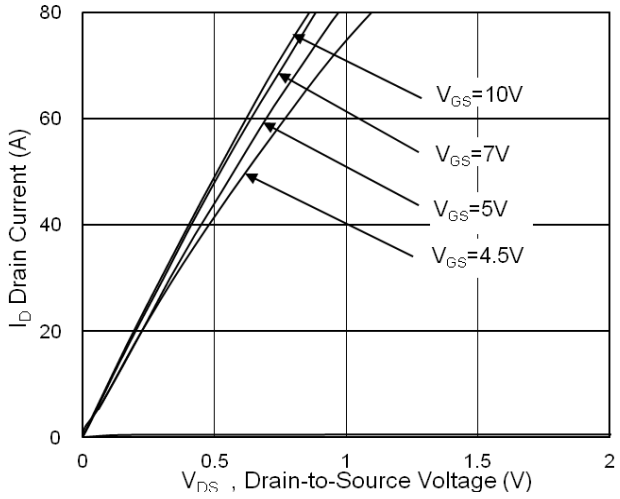


Fig.1 Typical Output Characteristics

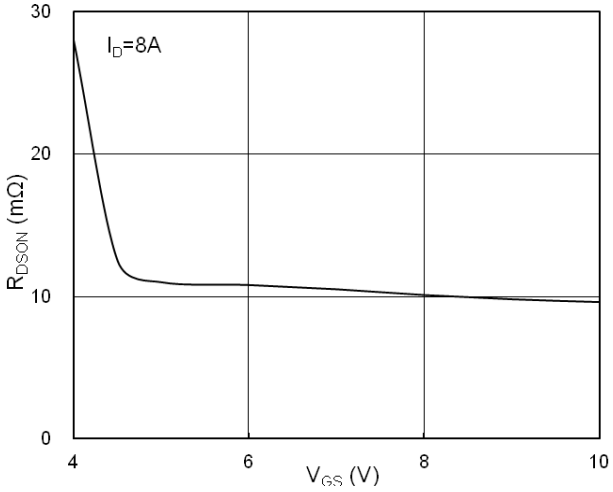


Fig.2 On-Resistance v.s Gate-Source

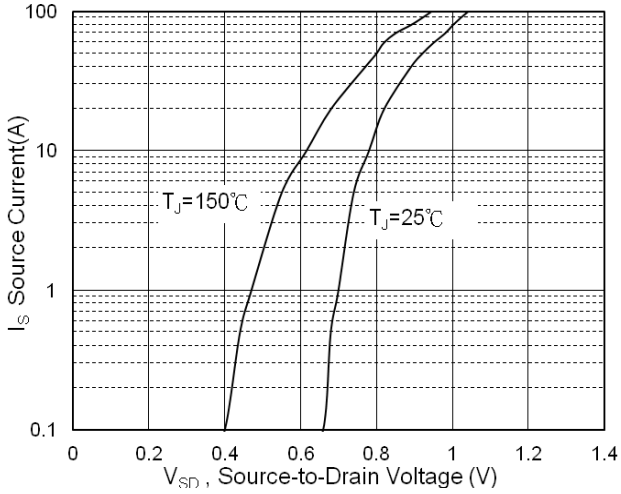


Fig.3 Forward Characteristics of Reverse

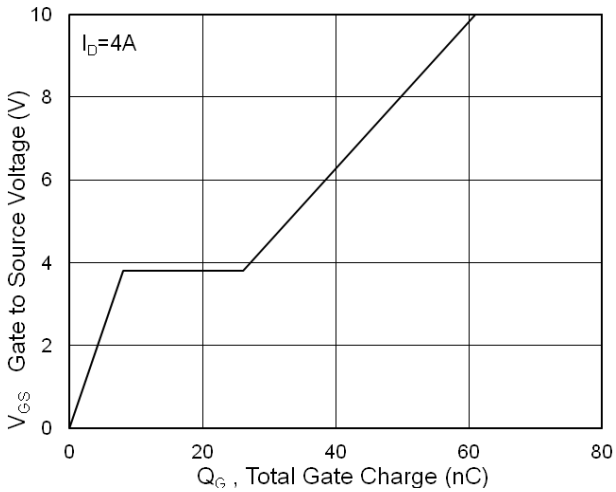


Fig.4 Gate-Charge Characteristics

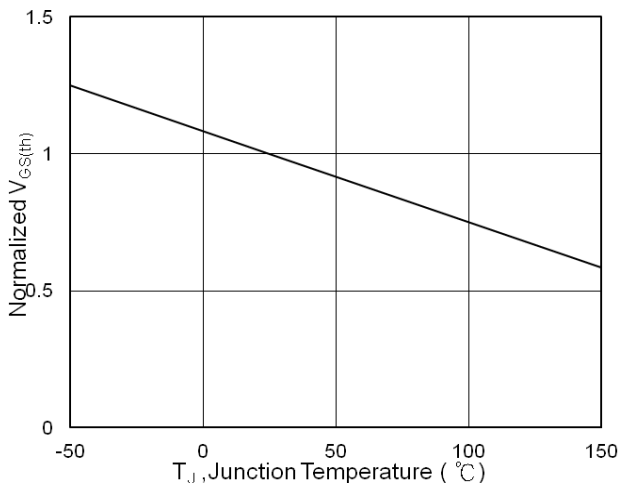


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

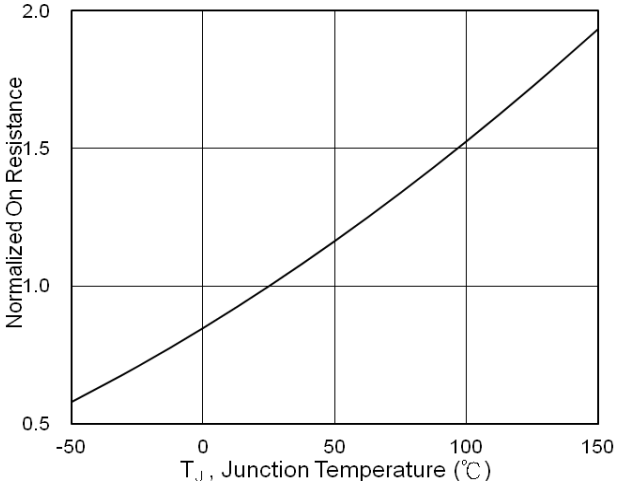


Fig.6 Normalized R_{DSON} vs. T_J

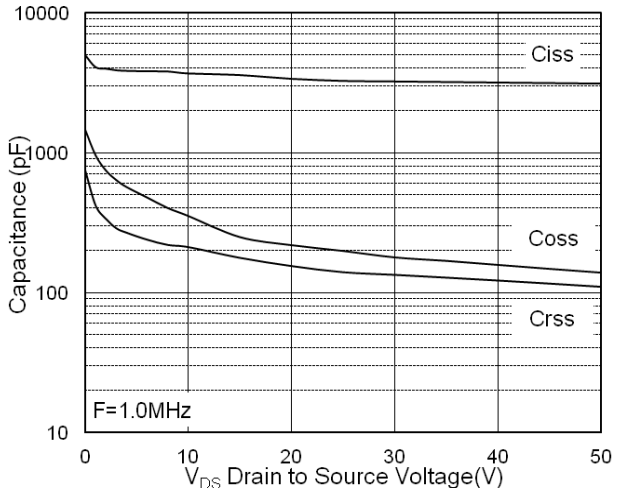


Fig.7 Capacitance

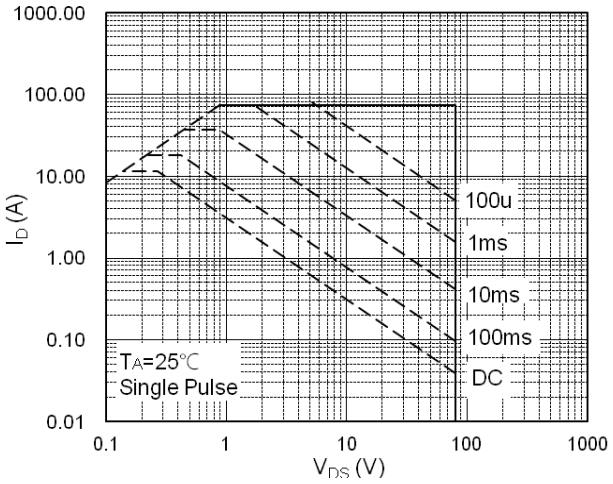


Fig.8 Safe Operating Area

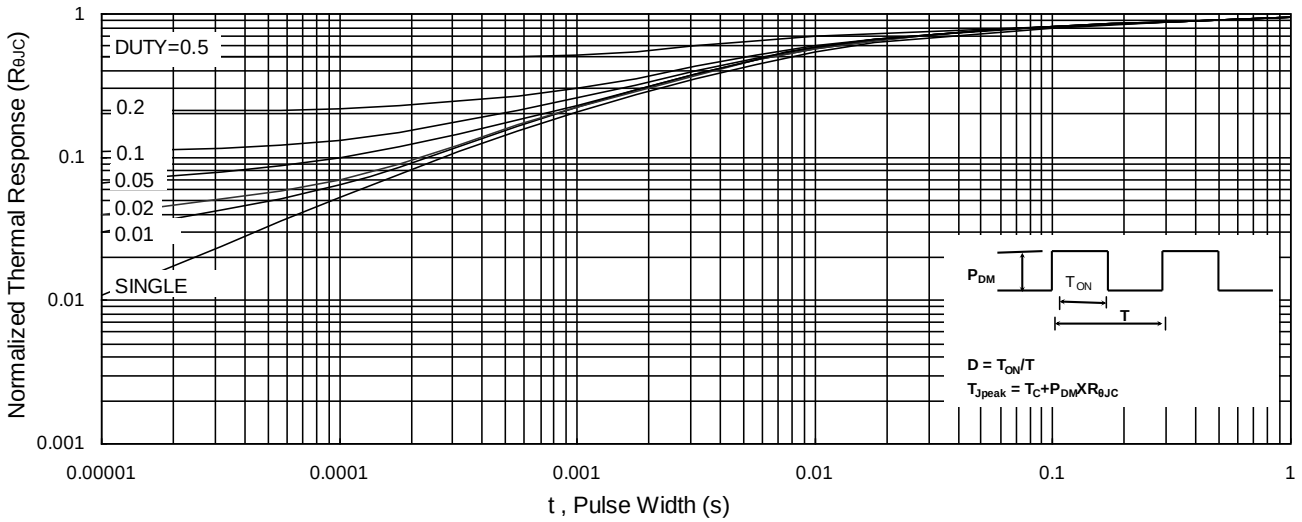


Fig.9 Normalized Maximum Transient Thermal Impedance

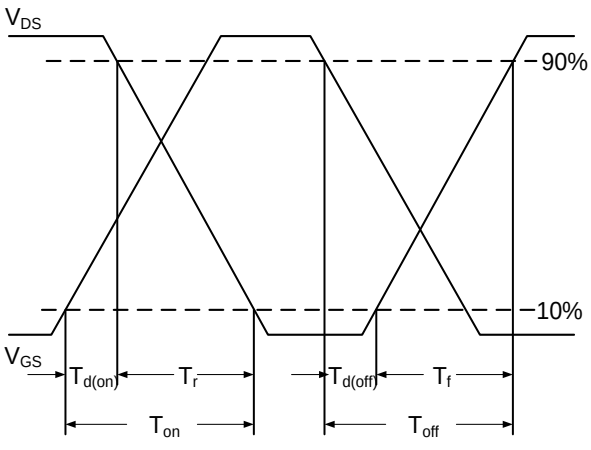


Fig.10 Switching Time Waveform

$$EAS = \frac{1}{2} L \times I_{AS}^2 \times \frac{BV_{DSS}}{BV_{DSS}-V_{DD}}$$

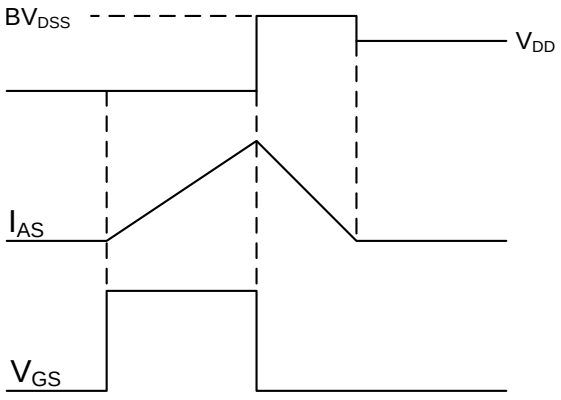


Fig.11 Unclamped Inductive Switching Waveform